1. General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4350Z

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- · High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- DC/DC converters
- · Supply line switching
- Battery charger
- LED backlighting
- Linear voltage regulation (LDO)
- Driver in low supply voltage applications, e.g. lamps, LEDs
- · Inductive load driver (for example relays, buzzers, motors)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	-50	V
Ic	collector current			-	-	-3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-5	Α
R _{CEsat}	collector-emitter saturation resistance	I _C = -2 A; I _B = -200 mA; T _{amb} = 25 °C	[1]	-	120	150	mΩ

[1] Pulsed test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$



50 V, 3 A PNP low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	C
2	С	collector		В—
3	E	emitter		
4	С	collector	☐1 ☐2 ☐3 SC-73 (SOT223)	Ë sym132

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS5350Z	SC-73	plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223		

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5350Z	PB5350

50 V, 3 A PNP low VCEsat (BISS) transistor

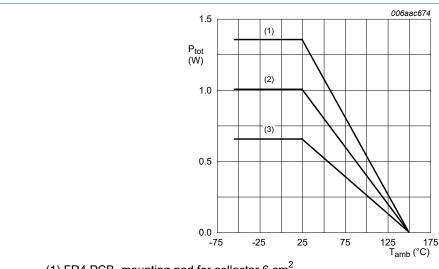
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-60	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-5	А
I _{BM}	peak base current			-	-1	А
P _{tot}	total power dissipation		[1]	-	0.65	W
			[2]	-	1	W
			[3] [4]	-	1.35	W
			[5]	-	2	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 Printed-Circuit Board (PCB), 35 µm single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 6 cm². [3]
- Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 1 cm² Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) FR4 PCB, mounting pad for collector 6 cm² (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Power derating curves Fig. 1.

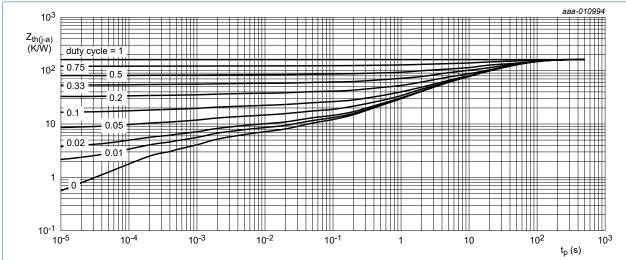
50 V, 3 A PNP low VCEsat (BISS) transistor

9. Thermal characteristics

Table 6. Thermal characteristics

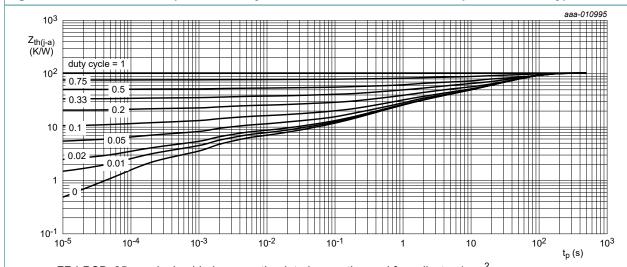
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
uiy-a)	thermal resistance from	in free air	[1]	-	-	192	K/W	
	junction to ambient	[2]	-	-	125	K/W		
			[3] [4]	-	-	92	K/W	
			[5]	-	-	62.5	K/W	
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	16	K/W	

- Device mounted on an FR4 PCB, 35 μm single-sided copper, tin-plated and standard footprint.
- [2]
- Device mounted on an FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 6 cm². Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 1 cm². [3]
- [4]
- Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 6 cm². [5]



FR4 PCB, 35 µm single-sided copper, tin-plated and standard footprint.

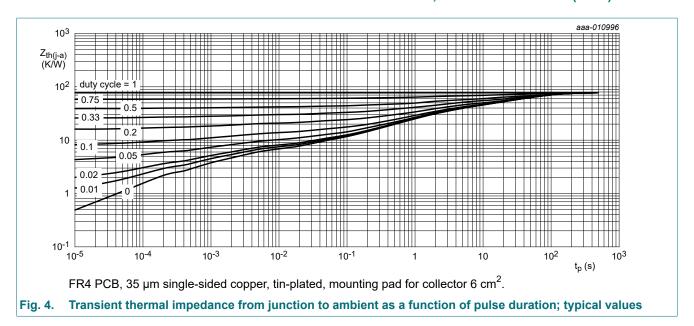
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 1 cm².

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 3 A PNP low VCEsat (BISS) transistor



10. Characteristics

Table 7. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	I _C = -100 μA; I _E = 0 A		-60	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = -10 \text{ mA}; I_B = 0 \text{ A}$		-50	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage (collector open)	I _E = -100 μA; I _C = 0 A		-6	-	-	V
I _{CBO}	collector-base cut-off	V _{CB} = -50 V; I _E = 0 A		-	-	-100	nA
	current	V _{CB} = -50 V; I _E = 0 A; T _j = 150 °C		-	-	-50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A		-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -2 V; I _C = -500 mA		200	-	-	
		V _{CE} = -2 V; I _C = -1 A	[1]	200	-	-	
		V _{CE} = -2 V; I _C = -2 A	[1]	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -500 mA; I _B = -50 mA		-	-	-100	mV
		I _C = -1 A; I _B = -50 mA		-	-	-180	mV
		I _C = -2 A; I _B = -200 mA	[1]	-	-	-300	mV
R _{CEsat}	collector-emitter saturation resistance	$I_C = -2 \text{ A}$; $I_B = -200 \text{ mA}$; $T_{amb} = 25 \text{ °C}$	[1]	-	120	150	mΩ
V_{BEsat}	base-emitter saturation voltage	I _C = -2 A; I _B = -200 mA	[1]	-	-	-1.2	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = -2 V; I _C = -1 A; T _{amb} = 25 °C	[1]	-	-	-1.1	V
f _T	transition frequency	V _{CE} = -5 V; I _C = -100 mA; f = 100 MHz		100	-	-	MHz

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz	-	-	40	pF

[1] Pulsed test: $t_p \le 300 \,\mu s$; $\delta \le 0.02$

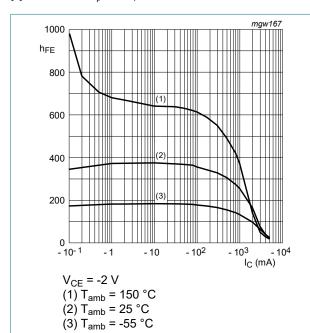


Fig. 5. DC current gain as a function of collector current; typical values

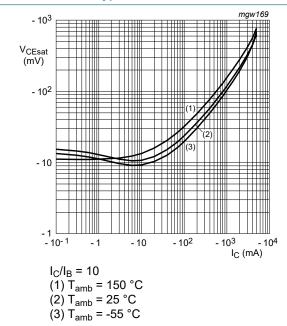


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

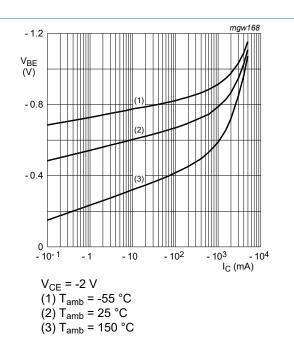


Fig. 6. Base-emitter voltage as a function of collector current; typical values

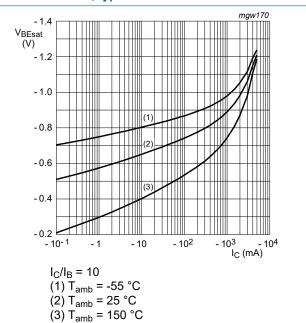
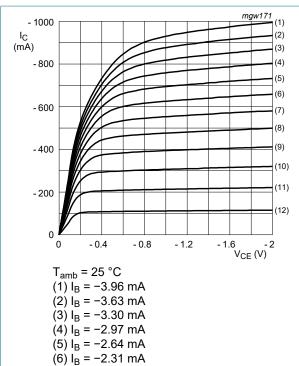


Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

50 V, 3 A PNP low VCEsat (BISS) transistor



 $(7) I_B = -1.98 \text{ mA}$ (8) $I_B = -1.65 \text{ mA}$

(9) $I_B = -1.32 \text{ mA}$

 $(10) I_B = -0.99 \text{ mA}$

 $(11) I_B = -0.66 \text{ mA}$

(12) $I_B = -0.33 \text{ mA}$

Fig. 9. Collector current as a function of collectoremitter voltage; typical values

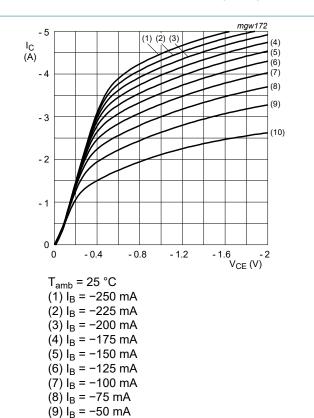
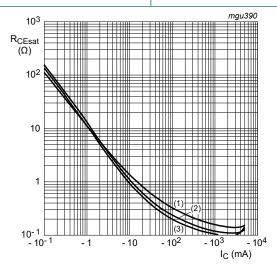


Fig. 10. Collector current as a function of collectoremitter voltage; typical values

(10) $I_B = -25 \text{ mA}$



 $I_C/I_B = 20$

 $(1) T_{amb} = 150 °C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55$ °C

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

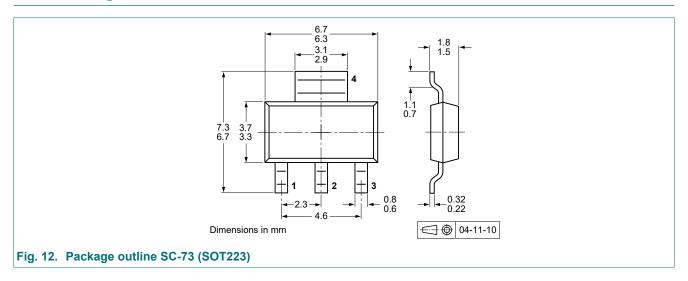
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11. Test information

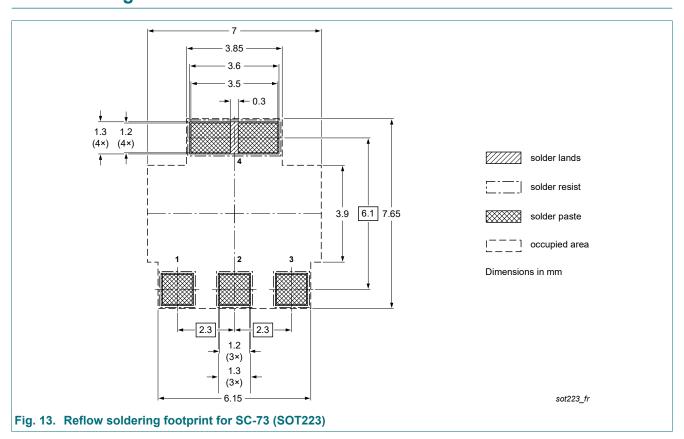
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

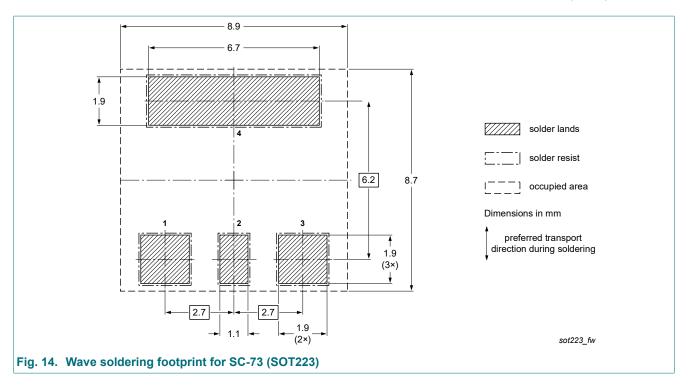
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Cuparadaa
			Change notice	Supersedes
PBSS5350Z v.5	20191118	Product data sheet	-	PBSS5350Z v.4
Modifications:	Nexperia.	nis data sheet has been rede e been adapted to the new c		
PBSS5350Z v.4	20030513	Product data sheet	-	PBSS5350Z v.3
PBSS5350Z v.3	20030120	Product data sheet	-	PBSS5350Z v.2
PBSS5350Z v.2	20011113	Product data sheet	-	PBSS5350Z v.1
PBSS5350Z v.1	20010717	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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